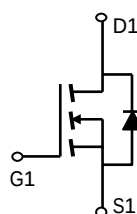
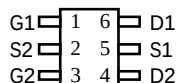
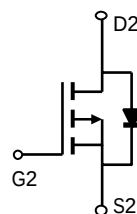


AO6605
Complementary Enhancement Mode Field Effect Transistor
General Description

The AO6605 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. *Standard Product AO6605 is Pb-free (meets ROHS & Sony 259 specifications). AO6605L is a Green Product ordering option. AO6605 and AO6605L are electrically identical.*

Features

n-channel	p-channel
V_{DS} (V) = 20V	-20V
I_D = 1.9A (V_{GS} = 4.5V)	-2.5A
$R_{DS(ON)}$	
< 200m Ω	< 97m Ω (V_{GS} = 4.5V)
< 270m Ω	< 130m Ω (V_{GS} = 2.5V)
< 400m Ω	< 190m Ω (V_{GS} = 1.8V)

**TSOP6
Top View**

n-channel

p-channel
Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 8	± 8	V
Continuous Drain Current ^A	I_D	1.7	-2.5	A
$T_A=25^\circ\text{C}$				
$T_A=70^\circ\text{C}$		1.4	-2.0	
Pulsed Drain Current ^B	I_{DM}	15	-15	
Power Dissipation	P_D	1.15	1.15	W
$T_A=25^\circ\text{C}$				
$T_A=70^\circ\text{C}$		0.73	0.73	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	78	110	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	106	150	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	64	80	$^\circ\text{C/W}$
Steady-State				

N-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			25	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.55	0.9	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	5			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =1.9A T _J =125°C		165 230	200 280	mΩ
		V _{GS} =2.5V, I _D =1.6A		225	270	mΩ
		V _{GS} =1.8V, I _D =1.3A		325	400	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =1.9A		2.8		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.88	1	V
I _S	Maximum Body-Diode Continuous Current				0.4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		101	125	pF
C _{oss}	Output Capacitance			17		pF
C _{rss}	Reverse Transfer Capacitance			14		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3	4	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =1.9A		1.6	2	nC
Q _{gs}	Gate Source Charge			0.2		nC
Q _{gd}	Gate Drain Charge			0.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =5.3Ω, R _{GEN} =3Ω		3.2		ns
t _r	Turn-On Rise Time			4		ns
t _{D(off)}	Turn-Off DelayTime			15.5		ns
t _f	Turn-Off Fall Time			2.4		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =1.9A, dI/dt=100A/μs		6.7	16	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =1.9A, dI/dt=100A/μs		1.6		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev2: August 2005

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N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

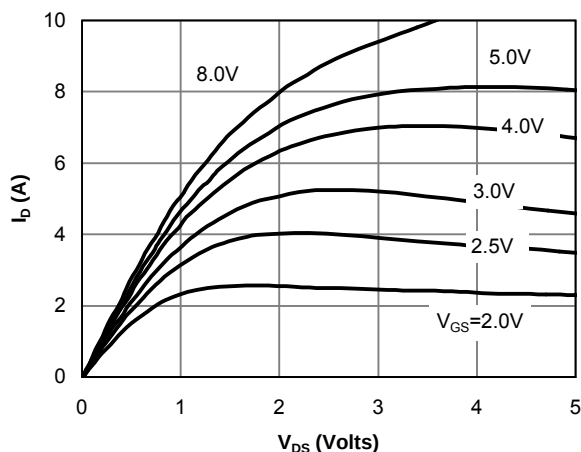


Fig 1: On-Region Characteristics

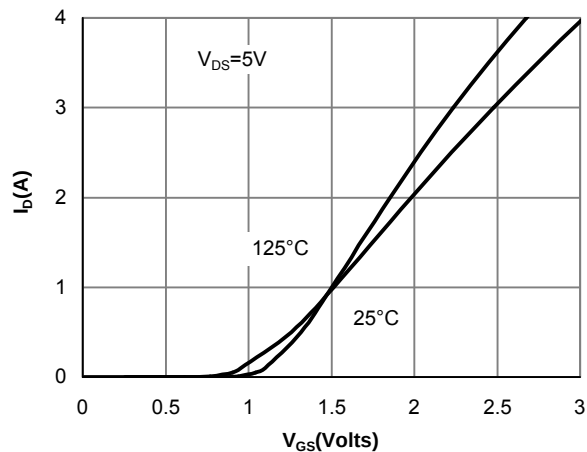


Figure 2: Transfer Characteristics

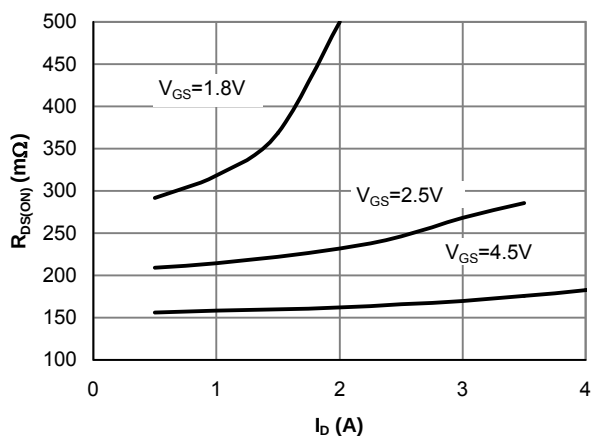


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

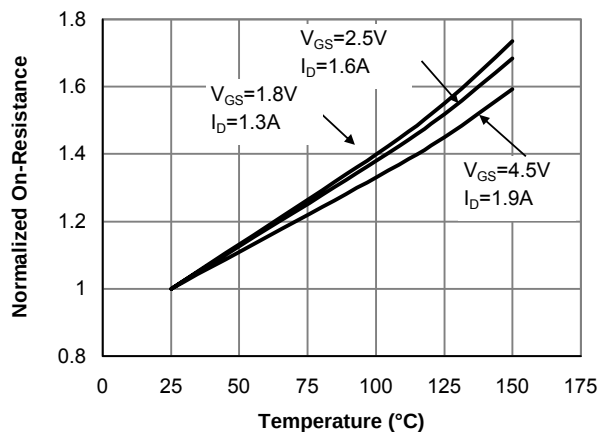


Figure 4: On-Resistance vs. Junction Temperature

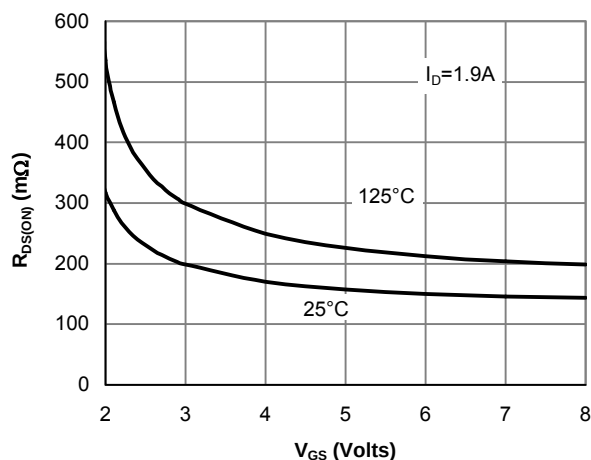


Figure 5: On-Resistance vs. Gate-Source Voltage

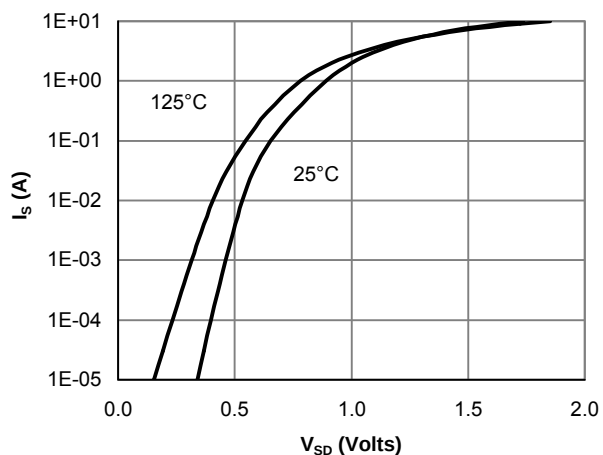


Figure 6: Body-Diode Characteristics

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

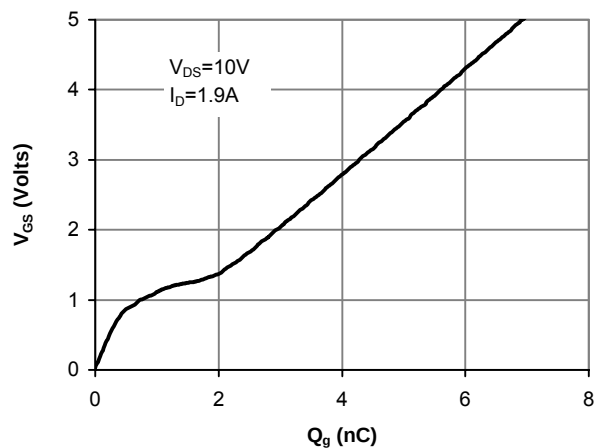


Figure 7: Gate-Charge Characteristics

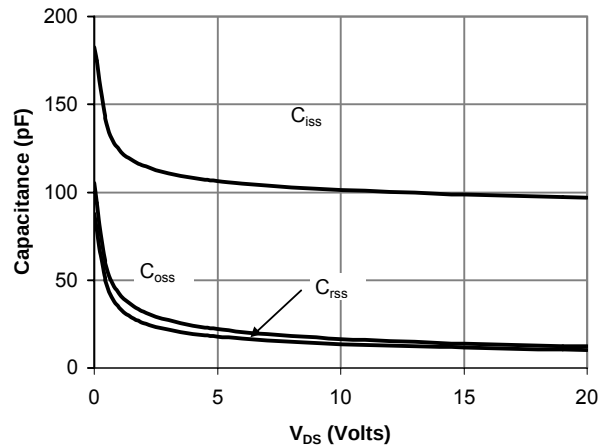


Figure 8: Capacitance Characteristics

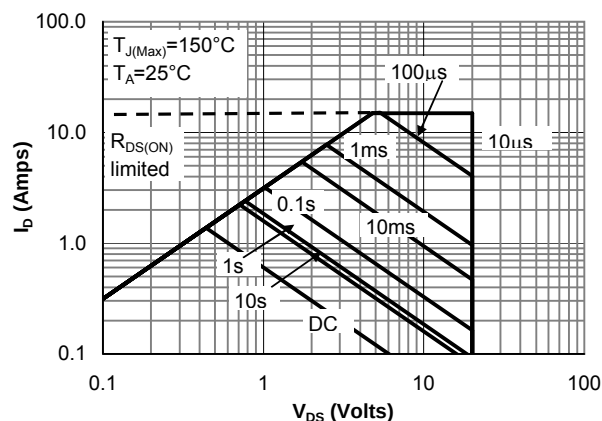


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

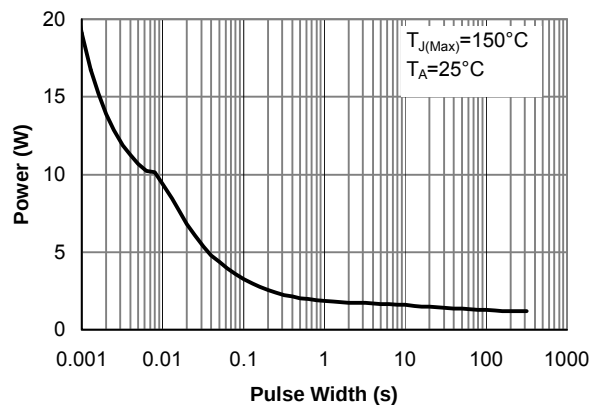


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

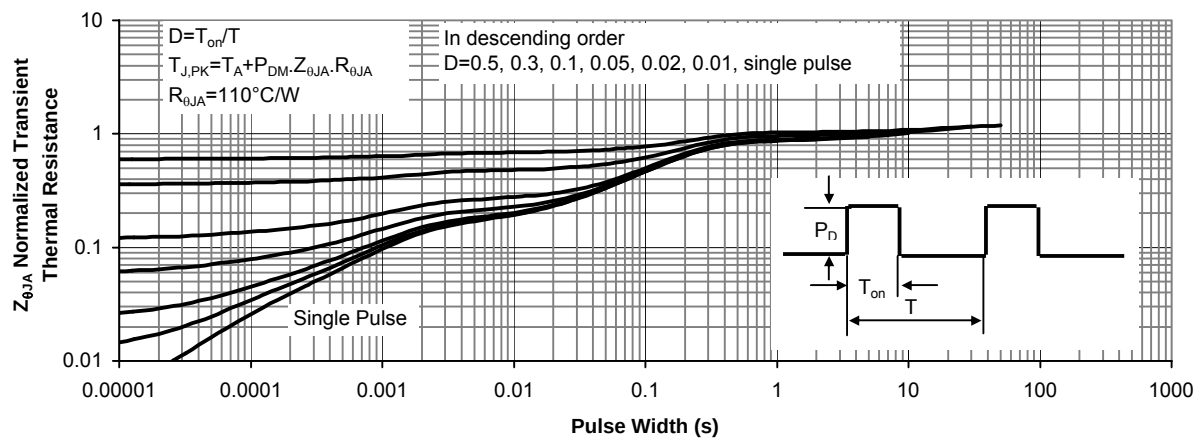


Figure 11: Normalized Maximum Transient Thermal Impedance

P-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	-0.55	-1	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-2.5A T _J =125°C		81 111	97 135	mΩ
		V _{GS} =-2.5V, I _D =-2A		108	130	mΩ
		V _{GS} =-1.8V, I _D =-1A		146	190	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	4	6		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.78	-1	V
I _S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		540	700	pF
C _{oss}	Output Capacitance			72		pF
C _{rss}	Reverse Transfer Capacitance			49		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		15	19.5	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-2.5A		6.1	7.5	nC
Q _{gs}	Gate Source Charge			0.6		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =3.9Ω, R _{GEN} =3Ω		12		ns
t _r	Turn-On Rise Time			15		ns
t _{D(off)}	Turn-Off DelayTime			49		ns
t _f	Turn-Off Fall Time			27		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-2.5A, dI/dt=100A/μs		22	26	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-2.5A, dI/dt=100A/μs		16		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

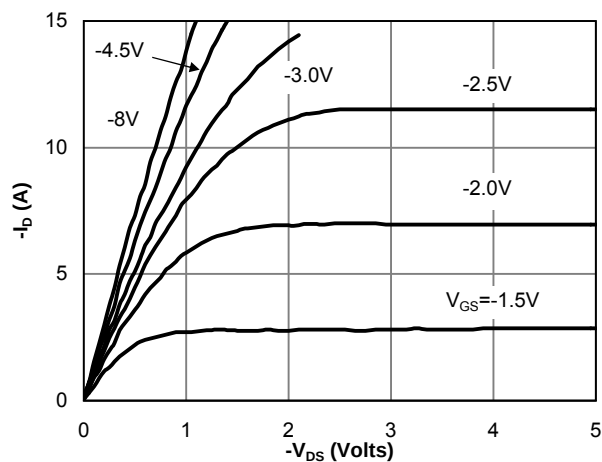


Fig 1: On-Region Characteristics

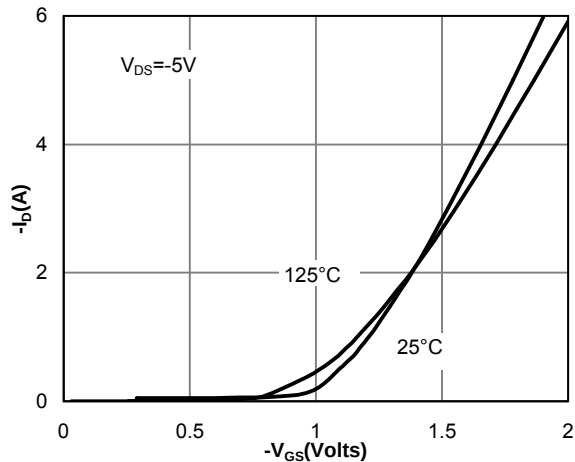


Figure 2: Transfer Characteristics

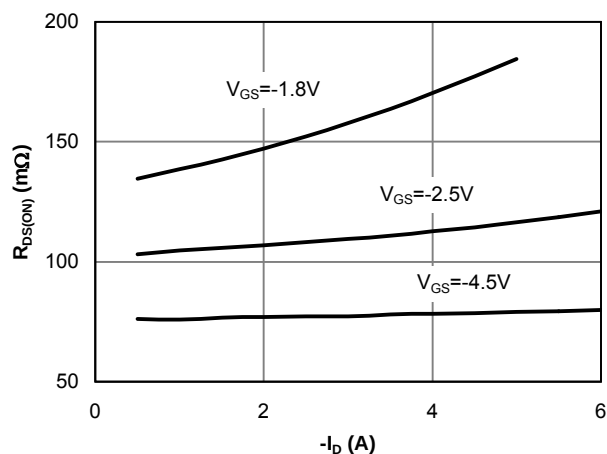


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

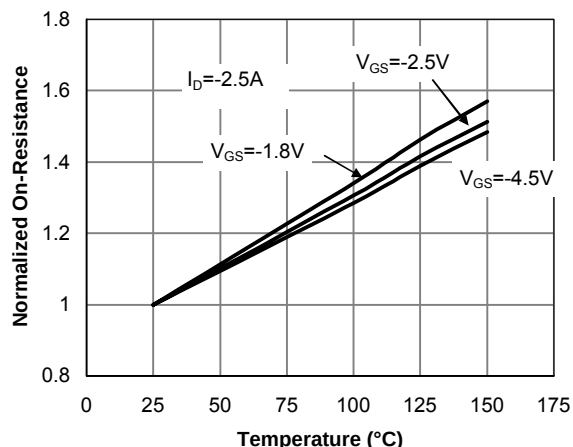


Figure 4: On-Resistance vs. Junction Temperature

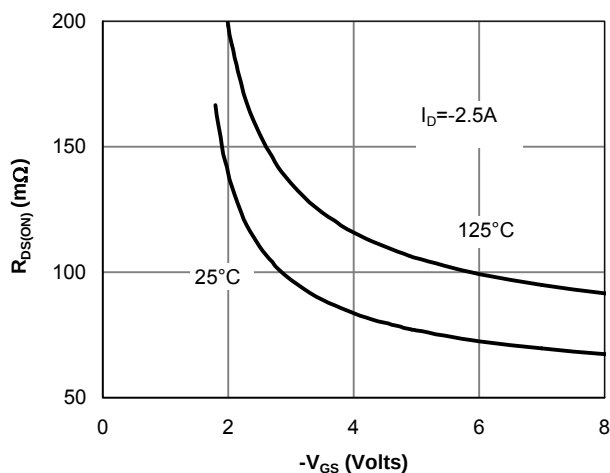


Figure 5: On-Resistance vs. Gate-Source Voltage

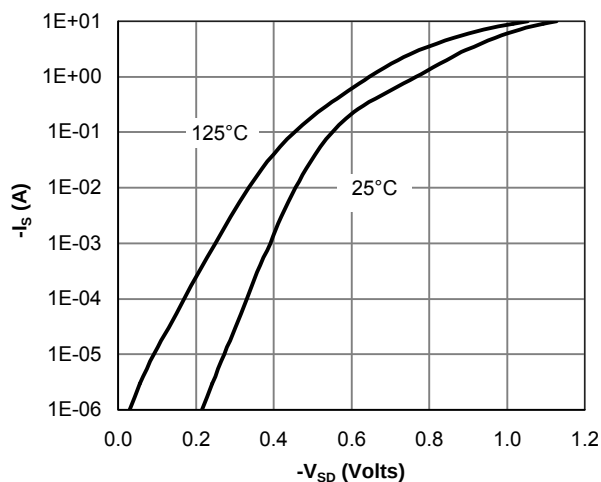


Figure 6: Body-Diode Characteristics

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

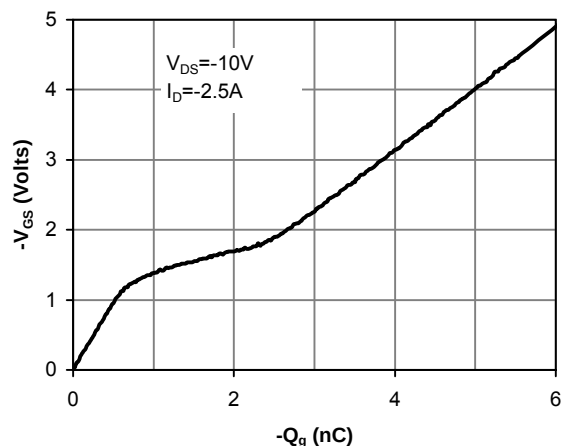


Figure 7: Gate-Charge Characteristics

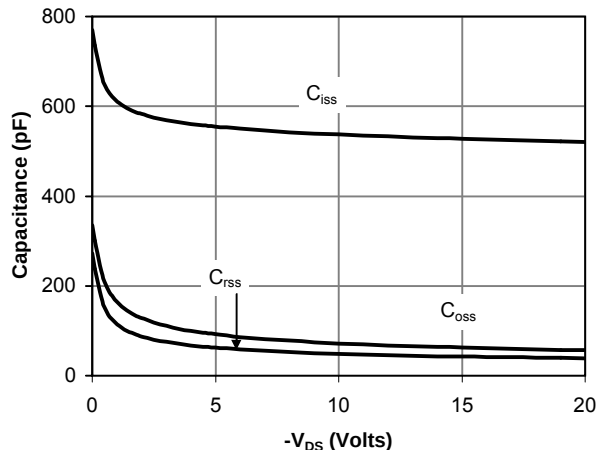


Figure 8: Capacitance Characteristics

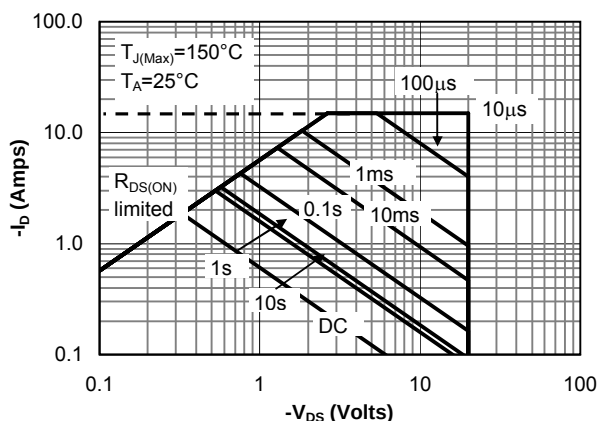


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

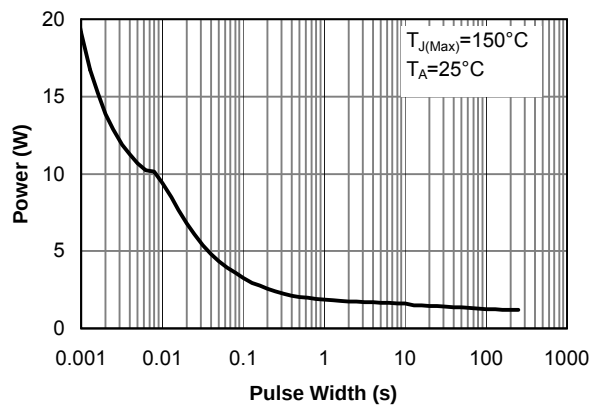


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

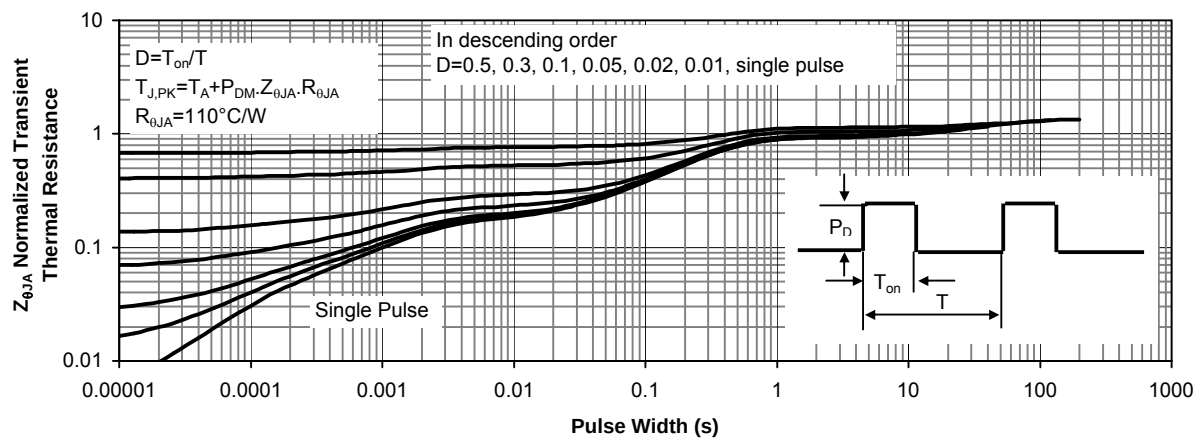


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